NEC

NPN SILICON POWER TRANSISTORS

2SC2690,2SC2690A

DESCRIPTION

The 2SC2690, 2SC2690A are general purpose transistors designed for use in audio and radio frequency power amplifiers.

FEATURES

- Suitable for use in driver stage of 50 to 100 W audio amplifiers and output stage of TV vertical deflection circuit.
- High Voltage and High f_T

 V_{CEO} = 120 V/160 V (2SC2690, 2SC2690A) f_{T} = 175 MHz (@V_{CE} = 5.0 V, I_C = 0.2 A)

 Complementary to the NEC 2SA1220, 2SA1220A PNP Transistors.

ABSOLUTE MAXIMUM RATINGS

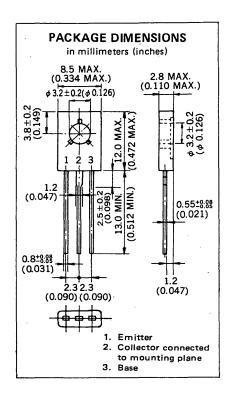
Maximum Temperatures

2SC2690 2SC2690A

V_{CBO}	Collector to Base Voltage 120		160	٧
V_{CEO}	Collector to Emitter Voltage120		160	٧
V_{EBO}	Emitter to Base Voltage	5.0		٧
IC(DC)	Collector Current	1.2		Α
I _{C(pulse)} *	Collector Current	2.5		Α
I _{B(DC)}	Base Current	0.3		Α

^{*} PW \leq 10 ms, Duty Cycle \leq 50 %

Maximum Voltages and Currents (Ta = 25 °C)



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1 **	DC Current Gain	35	150		_	V _{CE} = 5.0 V, I _C = 5.0 mA
hFE2 **	DC Current Gain	60	140	320	_	$V_{CE} = 5.0 \text{ V}, I_{C} = 0.3 \text{ A}$
f⊤	Gain Bandwidth Product		175		MHz	$V_{CE} = 5.0 \text{ V, } I_{C} = 0.2 \text{ A}$
C _{ob}	Output Capacitance		26		рF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$
Ісво	Collector Cutoff Current			1.0	μΑ	$V_{CB} = 120 \text{ V}, I_{E} = 0$
I _{EBO}	Emitter Cutoff Current			1.0	μΑ	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$
V _{CE(sat)} **	Collector Saturation Voltage		0.4	0.7	V	I _C = 1.0 A, I _B = 0.2 A
V _{BE(sat)} **	Base Saturation Voltage		1.0	1.3	٧	I _C = 1.0 A, I _B = 0.2 A

^{**} Pulsed / PW \leq 350 μ s, Duty Cycle \leq 2 %

Classification of h_{FE2}

Rank	. R	Q	Р
Range	60 to 120	100 to 200	160 to 320

Test Condition: VCE = 5.0 V, IC = 0.3 A

TYPICAL CHARACTERISTICS (Ta = 25 °C)

